

IRFR1018ETRPBF-VB Datasheet

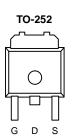
N-Channel 60 V (D-S) MOSFET

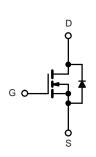
| PRODUCT SUMMARY | | | | | |
|---------------------|----------------------------------|---------------------------------|--|--|--|
| V _{DS} (V) | $R_{DS(on)}(\Omega)$ | I _D (A) ^a | | | |
| 60 | 0.010 at V _{GS} = 10 V | 58 | | | |
| 60 | 0.013 at V _{GS} = 4.5 V | 56 | | | |

FEATURES

- 175 °C Junction Temperature
 TrenchFET[®] Power MOSFET
- Material categorization:







N-Channel MOSFET

| ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted) | | | | | | | |
|---|-------------------------|-----------------------------------|--------------------------------------|----|--|--|--|
| Parameter | Symbol | Limit | Unit | | | | |
| Gate-Source Voltage | V_{GS} | ± 20 | V | | | | |
| Continuous Danis Comment /T 475 90\b | T _C = 25 °C | I- | 58 | | | | |
| Continuous Drain Current (T _J = 175 °C) ^b | T _C = 100 °C | l _D | 48 ^a | 7 | | | |
| Pulsed Drain Current | I _{DM} | 100 | A | | | | |
| Continuous Source Current (Diode Conduction) | I _S | 50 ^a | | | | | |
| Avalanche Current | I _{AS} 50 | | | | | | |
| Single Avalanche Energy (Duty Cycle ≤ 1 %) | L = 0.1 mH | E _{AS} | 125 | mJ | | | |
| Maximum Dawar Dissination | T _C = 25 °C | P _D | 136 | W | | | |
| Maximum Power Dissipation | T _A = 25 °C |] 'D | 3 ^b , 8.3 ^{b, c} |] | | | |
| Operating Junction and Storage Temperature Range | | T _J , T _{stg} | - 55 to 175 | °C | | | |

| THERMAL RESISTANCE RATINGS | | | | | | | |
|--|--------------|-------------------|---------|---------|------|--|--|
| Parameter | | Symbol | Typical | Maximum | Unit | | |
| Maximum Junction-to-Ambient ^a | t ≤ 10 sec | R _{thJA} | 15 | 18 | °C/W | | |
| waximum Junction-to-Ambient* | Steady State | | 40 | 50 | | | |
| Maximum Junction-to-Case | | R _{thJC} | 0.85 | 1.1 | | | |

Notes:

- a. Package limited.
- b. Surface mounted on 1" x 1" FR4 board.
- c. $t \le 10$ s.



| Parameter | Symbol | Test Conditions | Min. | Typ. ^a | Max. | Unit | |
|---|---------------------|--|------|-------------------|----------|------|--|
| Static | | | l . | | <u> </u> | | |
| Drain-Source Breakdown Voltage | V _{DS} | $V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$ | 60 | | | V | |
| Gate Threshold Voltage | V _{GS(th)} | $V_{DS} = V_{GS}, I_{D} = 250 \mu A$ | 1 | 2 | 3 | V | |
| Gate-Body Leakage | I _{GSS} | $V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$ | | | ± 100 | nA | |
| | | V _{DS} = 60 V, V _{GS} = 0 V | 1 1 | | 1 | | |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{DS} = 60 V, V _{GS} = 0 V, T _J = 125 °C | | | 50 | μА | |
| | | V _{DS} = 60 V, V _{GS} = 0 V, T _J = 175 °C | | | 250 | | |
| On-State Drain Current ^b | I _{D(on)} | V _{DS} = 5 V, V _{GS} = 10 V | 60 | | | Α | |
| | | V _{GS} = 10 V, I _D = 20 A | | 0.010 | | | |
| 5 1 6 9 9 1 5 1 1 b | D | V _{GS} = 10 V, I _D = 20 A, T _J = 125 °C | | 0.016 | | Ω | |
| Drain-Source On-State Resistance ^b | R _{DS(on)} | V _{GS} = 10 V, I _D = 20 A, T _J = 175 °C | | 0.020 | 0.020 | | |
| | | $V_{GS} = 4.5 \text{ V}, I_D = 15 \text{ A}$ | | 0.013 | | | |
| Forward Transconductance ^b | 9 _{fs} | $V_{DS} = 15 \text{ V}, I_{D} = 20 \text{ A}$ | | 60 | | S | |
| Dynamic | | | • | • | | | |
| Input Capacitance | C _{iss} | | | 2650 | | pF | |
| Output Capacitance | C _{oss} | $V_{GS} = 0 \text{ V}, V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$ | | 470 | | | |
| Reverse Transfer Capacitance | C _{rss} | | | 225 | | | |
| Total Gate Charge ^c | Qg | | | 47 | 70 | | |
| Gate-Source Charge ^c | Q_{gs} | $V_{DS} = 30 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 50 \text{ A}$ | | 10 | | nC | |
| Gate-Drain Charge ^c | Q _{gd} | | | 12 | |] | |
| Turn-On Delay Time ^c | t _{d(on)} | | | 10 | 20 | | |
| Rise Time ^c | t _r | $V_{DD} = 30 \text{ V}, R_{L} = 0.6 \Omega$ | | 15 | 25 | 20 | |
| Turn-Off Delay Time ^c | t _{d(off)} | $I_D\cong 50$ A, V_{GEN} = 10 V, R_g = 2.5 Ω | | 35 | 50 | ns | |
| Fall Time ^c | t _f | | | 20 | 30 | | |
| Source-Drain Diode Ratings and Cha | aracteristics (| T _C = 25 °C) | | | | | |
| Pulsed Current | I _{SM} | | | | 60 | Α | |
| Diode Forward Voltage | V_{SD} | I _F = 20 A, V _{GS} = 0 V | | 1 | 1.5 | V | |
| Reverse Recovery Time | t _{rr} | I _F = 20 A, di/dt = 100 A/μs | | 45 | 100 | ns | |

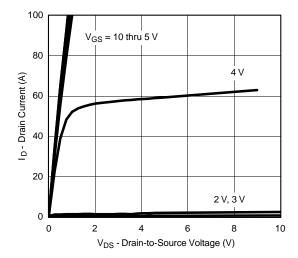
Notes:

- a. For design aid only; not subject to production testing.
- b. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



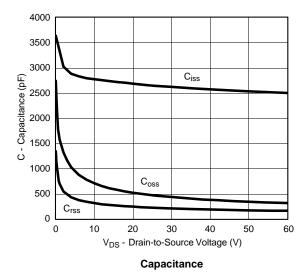
TYPICAL CHARACTERISTICS (25 °C unless noted)



Output Characteristics



Transconductance



100

80

(V) triangle 60

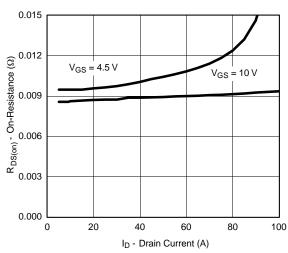
T_C = 125 °C

25 °C

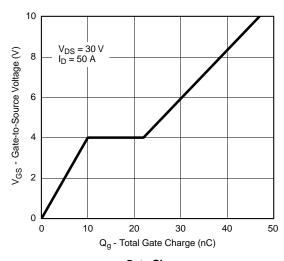
-55 °C

V_{GS} - Gate-to-Source Voltage (V)

Transfer Characteristics



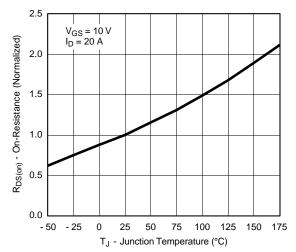
On-Resistance vs. Drain Current



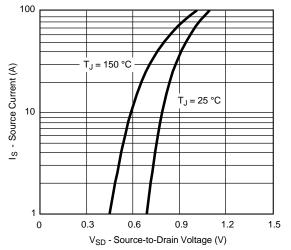
Gate Charge



TYPICAL CHARACTERISTICS (25 °C unless noted)



On-Resistance vs. Junction Temperature

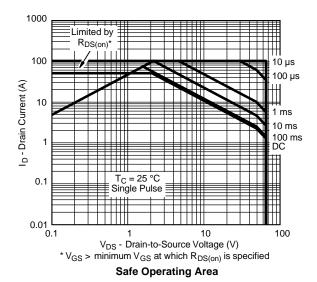


Source-Drain Diode Forward Voltage

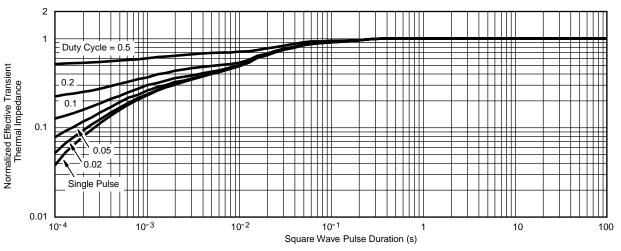


THERMAL RATINGS





Maximum Drain Current vs. Ambient Temperature



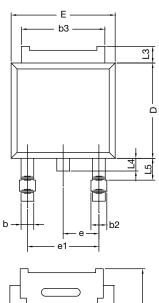
Normalized Thermal Transient Impedance, Junction-to-Case

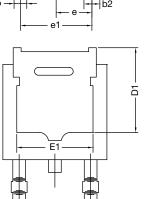
服务热线:400-655-8788

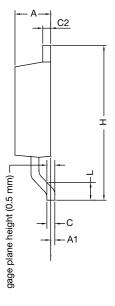
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TO-252AA CASE OUTLINE







| | MILLIMETERS | | INC | HES | |
|---------------------------------|-------------|-------|-----------|-------|--|
| DIM. | MIN. | MAX. | MIN. | MAX. | |
| Α | 2.18 | 2.38 | 0.086 | 0.094 | |
| A1 | - | 0.127 | - | 0.005 | |
| b | 0.64 | 0.88 | 0.025 | 0.035 | |
| b2 | 0.76 | 1.14 | 0.030 | 0.045 | |
| b3 | 4.95 | 5.46 | 0.195 | 0.215 | |
| С | 0.46 | 0.61 | 0.018 | 0.024 | |
| C2 | 0.46 | 0.89 | 0.018 | 0.035 | |
| D | 5.97 | 6.22 | 0.235 | 0.245 | |
| D1 | 5.21 | - | 0.205 | - | |
| E | 6.35 | 6.73 | 0.250 | 0.265 | |
| E1 | 4.32 | - | 0.170 | - | |
| Н | 9.40 | 10.41 | 0.370 | 0.410 | |
| е | 2.28 BSC | | 0.090 BSC | | |
| e1 | 4.56 | BSC | 0.180 | BSC | |
| L | 1.40 | 1.78 | 0.055 | 0.070 | |
| L3 | 0.89 | 1.27 | 0.035 | 0.050 | |
| L4 | - | 1.02 | - | 0.040 | |
| L5 | 1.14 | 1.52 | 0.045 | 0.060 | |
| ECN: X12-0247-Rev. M, 24-Dec-12 | | | | | |

ECN: X12-0247-Rev. M, 24-Dec-12 DWG: 5347

Note

• Dimension L3 is for reference only.



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